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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	24MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	25
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 7x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s207k6t3ctr

List of figures

Figure 1.	STM8S20xxx block diagram	12
Figure 2.	Flash memory organization	
Figure 3.	LQFP 80-pin pinout	
Figure 4.	LQFP 64-pin pinout	
Figure 5.	LQFP 48-pin pinout	
Figure 6.	LQFP 44-pin pinout	
Figure 7.	LQFP 32-pin pinout	
Figure 8.	Memory map	
Figure 9.	Supply current measurement conditions	
Figure 10.	Pin loading conditions	
Figure 11.	Pin input voltage	
Figure 12.	f _{CPUmax} versus V _{DD}	
Figure 13.	External capacitor C _{FXT}	57
Figure 14.	Typ. $I_{DD(RUN)}$ vs V_{DD} , HSI RC osc, $f_{CPU} = 16$ MHz	
Figure 15.	Typ. $I_{DD(WFI)}$ vs V_{DD} , HSI RC osc, $f_{CPU} = 16$ MHz	
Figure 16.	HSE external clock source	
Figure 17.	HSE oscillator circuit diagram	
Figure 18.	Typical HSI frequency variation vs V _{DD} at 4 temperatures	
Figure 19.	Typical LSI frequency variation vs V _{DD} @ 25 °C	
Figure 20.	Typical V_{IL} and V_{IH} vs V_{DD} @ 4 temperatures	
Figure 21.	Typical pull-up resistance vs V _{DD} @ 4 temperatures	
Figure 22.	Typical pull-up current vs V _{DD} @ 4 temperatures	
Figure 23.	Typ. V_{OL} @ $V_{DD} = 5$ V (standard ports)	
Figure 24.	Typ. V_{OL} @ V_{DD} = 3.3 V (standard ports)	
Figure 25.	Typ. V_{OL} @ V_{DD} = 5 V (true open drain ports)	
Figure 26.	Typ. V_{OL} @ V_{DD} = 3.3 V (true open drain ports)	
Figure 27.	Typ. V_{OL} @ V_{DD} = 5 V (high sink ports)	
Figure 28.	Typ. V_{OL} @ V_{DD} = 3.3 V (high sink ports)	
Figure 29.	Typ. $V_{DD} - V_{OH} @ V_{DD} = 5 V$ (standard ports)	
Figure 30.	Typ. $V_{DD} - V_{OH} @ V_{DD} = 3.3 \text{ V (standard ports)}$	
Figure 31.	Typ. $V_{DD} - V_{OH} @ V_{DD} = 5.3 \text{ (standard ports)}$	
Figure 31.	Typ. $V_{DD} - V_{OH} @ V_{DD} = 3.3 \text{ V (high sink ports)}$	
Figure 33.	Typical NRST V_{II} and V_{IH} vs V_{DD} @ 4 temperatures	
Figure 34.	Typical NRST pull-up resistance vs V _{DD} @ 4 temperatures	
Figure 35.	Typical NRST pull-up current vs V _{DD} @ 4 temperatures	
Figure 36.	Recommended reset pin protection	
Figure 30.	SPI timing diagram - slave mode and CPHA = 0	
-	SPI timing diagram - slave mode and CPHA = 1 ⁽¹⁾	01
Figure 38. Figure 39.	SPI timing diagram - master mode and GPHA = 1\(\frac{1}{2}\)	۱۰.۰۰۱ ده
0	Typical application with I ² C bus and timing diagram	01
Figure 40.	ADC accuracy characteristics	
Figure 41.		
Figure 42.	Typical application with ADC	
Figure 43.	LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package outline	
Figure 44.	LQFP80 recommended footprint	93
Figure 45.	LQFP80 marking example (package top view)	
Figure 46.	LQFP64 - 64-pin 14 mm x 14 mm low-profile quad flat package outline	
Figure 47.	LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline	
Figure 48.	LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint	97



2 Description

The STM8S20xxx performance line 8-bit microcontrollers offer from 32 to 128 Kbytes Flash program memory. They are referred to as high-density devices in the STM8S microcontroller family reference manual.

All STM8S20xxx devices provide the following benefits: reduced system cost, performance robustness, short development cycles, and product longevity.

The system cost is reduced thanks to an integrated true data EEPROM for up to 300 k write/erase cycles and a high system integration level with internal clock oscillators, watchdog, and brown-out reset.

Device performance is ensured by 20 MIPS at 24 MHz CPU clock frequency and enhanced characteristics which include robust I/O, independent watchdogs (with a separate clock source), and a clock security system.

Short development cycles are guaranteed due to application scalability across a common family product architecture with compatible pinout, memory map and modular peripherals. Full documentation is offered with a wide choice of development tools.

Product longevity is ensured in the STM8S family thanks to their advanced core which is made in a state-of-the art technology for applications with 2.95 V to 5.5 V operating supply.

577

The size of the UBC is programmable through the UBC option byte (*Table 13*.), in increments of 1 page (512 bytes) by programming the UBC option byte in ICP mode.

This divides the program memory into two areas:

- Main program memory: Up to 128 Kbytes minus UBC
- User-specific boot code (UBC): Configurable up to 128 Kbytes

The UBC area remains write-protected during in-application programming. This means that the MASS keys do not unlock the UBC area. It protects the memory used to store the boot program, specific code libraries, reset and interrupt vectors, the reset routine and usually the IAP and communication routines.

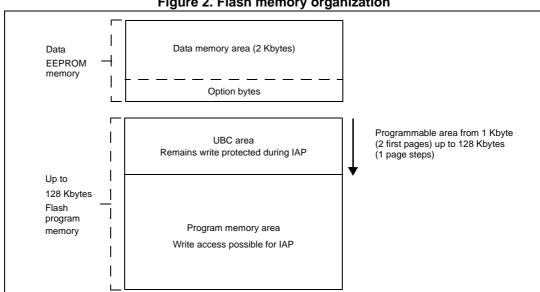


Figure 2. Flash memory organization

Read-out protection (ROP)

The read-out protection blocks reading and writing the Flash program memory and data EEPROM memory in ICP mode (and debug mode). Once the read-out protection is activated, any attempt to toggle its status triggers a global erase of the program and data memory. Even if no protection can be considered as totally unbreakable, the feature provides a very high level of protection for a general purpose microcontroller.

Independent watchdog timer

The independent watchdog peripheral can be used to resolve processor malfunctions due to hardware or software failures.

It is clocked by the 128 kHz LSI internal RC clock source, and thus stays active even in case of a CPU clock failure

The IWDG time base spans from 60 µs to 1 s.

4.8 Auto wakeup counter

- Used for auto wakeup from active halt mode
- Clock source: Internal 128 kHz internal low frequency RC oscillator or external clock
- LSI clock can be internally connected to TIM3 input capture channel 1 for calibration

4.9 Beeper

The beeper function outputs a signal on the BEEP pin for sound generation. The signal is in the range of 1, 2 or 4 kHz.

4.10 TIM1 - 16-bit advanced control timer

This is a high-end timer designed for a wide range of control applications. With its complementary outputs, dead-time control and center-aligned PWM capability, the field of applications is extended to motor control, lighting and half-bridge driver

- 16-bit up, down and up/down autoreload counter with 16-bit prescaler
- Four independent capture/compare channels (CAPCOM) configurable as input capture, output compare, PWM generation (edge and center aligned mode) and single pulse mode output
- Synchronization module to control the timer with external signals
- Break input to force the timer outputs into a defined state
- Three complementary outputs with adjustable dead time
- Encoder mode
- Interrupt sources: 3 x input capture/output compare, 1 x overflow/update, 1 x break

4.11 TIM2, TIM3 - 16-bit general purpose timers

- 16-bit autoreload (AR) up-counter
- 15-bit prescaler adjustable to fixed power of 2 ratios 1...32768
- Timers with 3 or 2 individually configurable capture/compare channels
- PWM mode
- Interrupt sources: 2 or 3 x input capture/output compare, 1 x overflow/update

5/

4.14.1 UART1

Main features

- One Mbit/s full duplex SCI
- SPI emulation
- High precision baud rate generator
- Smartcard emulation
- IrDA SIR encoder decoder
- LIN master mode
- · Single wire half duplex mode

Asynchronous communication (UART mode)

- Full duplex communication NRZ standard format (mark/space)
- Programmable transmit and receive baud rates up to 1 Mbit/s (f_{CPU}/16) and capable of following any standard baud rate regardless of the input frequency
- Separate enable bits for transmitter and receiver
- Two receiver wakeup modes:
 - Address bit (MSB)
 - Idle line (interrupt)
- Transmission error detection with interrupt generation
- Parity control

Synchronous communication

- Full duplex synchronous transfers
- SPI master operation
- 8-bit data communication
- Maximum speed: 1 Mbit/s at 16 MHz (f_{CPU}/16)

LIN master mode

- Emission: Generates 13-bit sync break frame
- Reception: Detects 11-bit break frame

4.14.2 UART3

Main features

- 1 Mbit/s full duplex SCI
- LIN master capable
- High precision baud rate generator

Table 6. Pin description (continued)

	Pin	num	ber		143			Inpu			Out	onti put				
LQFP80	LQFP64	LQFP48	LQFP44	LQFP32	Pin name	Туре	floating	ndw	Ext. interrupt	High sink	Speed	QO	ЬР	Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
31	27	19	18	13	PB3/AIN3	I/O	<u>X</u>	X	X		01	X	X	Port B3	Analog input 3	TIM1_ETR [AFR5]
32	28	20	19	14	PB2/AIN2	I/O	<u>x</u>	X	X		O1	X	X	Port B2	Analog input 2	TIM1_ CH3N [AFR5]
33	29	21	20	15	PB1/AIN1	I/O	<u>x</u>	х	Х		O1	X	Х	Port B1	Analog input 1	TIM1_ CH2N [AFR5]
34	30	22	21	16	PB0/AIN0	I/O	<u>x</u>	Х	Х		O1	Х	Х	Port B0	Analog input 0	TIM1_ CH1N [AFR5]
35	-	-	-	-	PH4/TIM1_ETR	I/O	<u>X</u>	Х			01	Х	Х	Port H4	Timer 1 - trigger input	
36	-	•	-	-	PH5/ TIM1_CH3N	I/O	<u>X</u>	X			O1	Х	Х	Port H5	Timer 1 - inverted channel 3	
37	-	-	1	•	PH6/ TIM1_CH2N	I/O	<u>X</u>	х			O1	Х	Х	Port H6	Timer 1 - inverted channel 2	
38	-	-	-	•	PH7/ TIM1_CH1N	I/O	<u>x</u>	х			O1	X	Х	Port H7	Timer 1 - inverted channel 2	
39	31	23	1	•	PE7/AIN8	I/O	<u>X</u>	Х	Χ		O1	Χ	Χ	Port E7	Analog input 8	
40	32	24	22	•	PE6/AIN9	I/O	<u>X</u>	Х	Х		01	Χ	Χ	Port E6	Analog input 9	
41	33	25	23	17	PE5/SPI_NSS	I/O	X	X	Х		01	Χ	X	Port E5	SPI master/slave select	
42	-	-	1	-	PC0/ADC_ETR	I/O	<u>x</u>	Х	Х		01	Х	Х	Port C0	ADC trigger input	
43	34	26	24	18	PC1/TIM1_CH1	I/O	<u>X</u>	Х	X	HS	О3	X	X	Port C1	Timer 1 - channel 1	
44	35	27	25	19	PC2/TIM1_CH2	I/O	<u>X</u>	Х	X	HS	О3	X	X	Port C2	Timer 1- channel 2	
45	36	28	26	20	PC3/TIM1_CH3	I/O	<u>x</u>	Х	Х	HS	О3	Х	Х	Port C3	Timer 1 - channel 3	

Table 6. Pin description (continued)

	Pin	num	ber					Inpu	t		Out					
LQFP80	LQFP64	LQFP48	LQFP44	LQFP32	Pin name	Туре	floating	mdm	Ext. interrupt	High sink	Speed	OD	ЬР	Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
46	37	29	1	21	PC4/TIM1_CH4	I/O	<u>X</u>	Χ	Χ	HS	О3	Х	Х	Port C4	Timer 1 - channel 4	
47	38	30	27	22	PC5/SPI_SCK	I/O	<u>X</u>	Х	Χ	HS	О3	Х	Χ	Port C5	SPI clock	
48	39	31	28	-	V _{SSIO_2}	S								I/O groun	d	
49	40	32	29	-	V_{DDIO_2}	S								I/O powe	supply	
50	41	33	30	23	PC6/SPI_MOSI	I/O	<u>X</u>	х	х	HS	О3	X	Х	Port C6	SPI master out/ slave in	
51	42	34	31	24	PC7/SPI_MISO	I/O	<u>X</u>	Х	Х	HS	О3	Х	Х	Port C7	SPI master in/ slave out	
52	43	35	32	1	PG0/CAN_TX ⁽²⁾	I/O	<u>X</u>	Х			01	Х	X	Port G0	beCAN transmit	
53	44	36	33	-	PG1/CAN_RX ⁽²⁾	I/O	<u>X</u>	Х			01	Х	Х	Port G1	beCAN receive	
54	45	-	-	-	PG2	I/O	<u>X</u>	Χ			O1	Χ	Χ	Port G2		
55	46	-	-	-	PG3	I/O	<u>X</u>	Х			O1	Х	Χ	Port G3		
56	47	ı	ı	•	PG4	I/O	<u>X</u>	Х			01	Х	Χ	Port G4		
57	48	1	1	1	PI0	I/O	<u>X</u>	Х			01	Х	Χ	Port I0		
58	-	-	-	-	PI1	I/O	<u>X</u>	Χ			O1	Х	Χ	Port I1		
59	-	-	1	-	PI2	I/O	<u>X</u>	Χ			01	Χ	Χ	Port I2		
60	-	-	1	-	PI3	I/O	<u>X</u>	Χ			01	Χ	Χ	Port I3		
61	-	-	-	-	PI4	I/O	<u>X</u>	Х			O1	Х	Χ	Port I4		
62	-	-	1	1	PI5	I/O	<u>X</u>	Χ			01	Χ	Χ	Port I5		
63	49	-	-	-	PG5	I/O	<u>X</u>	X			01	Χ	Χ	Port G5		
64	50	-	-	-	PG6	I/O	<u>X</u>	Χ			01	Χ	Х	Port G6		
65	51	-	-	-	PG7	I/O	<u>X</u>	Χ			01	Χ	Χ	Port G7		
66	52	-	1	-	PE4	I/O	<u>X</u>	Х	Х		01	Χ	Χ	Port E4		
67	53	37	1	1	PE3/TIM1_BKIN	I/O	<u>X</u>	Х	Х		01	Х	Х	Port E3	Timer 1 - break input	
68	54	38	34	-	PE2/I ² C_SDA	I/O	<u>X</u>		Χ		01	T ⁽³⁾		Port E2	I ² C data	



Table 9. General hardware register map

Address		able 9. General na		Reset		
Address	Block	Register label	Register name	status		
0x00 5050 to 0x00 5059		ı	Reserved area (10 bytes)			
0x00 505A		FLASH_CR1	Flash control register 1	0x00		
0x00 505B		FLASH_CR2	Flash control register 2	0x00		
0x00 505C		FLASH_NCR2	Flash complementary control register 2	0xFF		
0x00 505D	Flash	FLASH _FPR	Flash protection register	0x00		
0x00 505E		FLASH _NFPR	Flash complementary protection register	0xFF		
0x00 505F		FLASH_IAPSR	Flash in-application programming status register	0x00		
0x00 5060 to 0x00 5061			Reserved area (2 bytes)			
0x00 5062	Flash	FLASH _PUKR	_PUKR Flash Program memory unprotection register			
0x00 5063			Reserved area (1 byte)			
0x00 5064	Flash	FLASH _DUKR	0x00			
0x00 5065 to 0x00 509F		Reserved area (59 bytes)				
0x00 50A0	ITC	EXTI_CR1	External interrupt control register 1	0x00		
0x00 50A1		EXTI_CR2	External interrupt control register 2	0x00		
0x00 50A2 to 0x00 50B2		!	Reserved area (17 bytes)			
0x00 50B3	RST	RST_SR	Reset status register	0xXX ⁽¹⁾		
0x00 50B4 to 0x00 50BF			Reserved area (12 bytes)			
0x00 50C0	CLK	CLK_ICKR	Internal clock control register	0x01		
0x00 50C1	CLK	CLK_ECKR	External clock control register	0x00		
0x00 50C2			Reserved area (1 byte)			
0x00 50C3		CLK_CMSR	Clock master status register	0xE1		
0x00 50C4		CLK_SWR	Clock master switch register	0xE1		
0x00 50C5		CLK_SWCR	Clock switch control register	0xXX		
0x00 50C6		CLK_CKDIVR	Clock divider register	0x18		
0x00 50C7	CLK	CLK_PCKENR1	Peripheral clock gating register 1	0xFF		
0x00 50C8		CLK_CSSR	Clock security system register	0x00		
0x00 50C9		CLK_CCOR	Configurable clock control register	0x00		
0x00 50CA		CLK_PCKENR2	Peripheral clock gating register 2	0xFF		
0x00 50CB		CLK_CANCCR	CAN clock control register	0x00		



Table 16. Current characteristics

Symbol	Ratings	Max. ⁽¹⁾	Unit
I _{VDD}	Total current into V _{DD} power lines (source) ⁽²⁾	60	
I _{VSS}	Total current out of V _{SS} ground lines (sink) ⁽²⁾	60	
1.	Output current sunk by any I/O and control pin	20	
I _{IO}	Output current source by any I/Os and control pin	20	
	Total output current sourced (sum of all I/O and control pins) for devices with two V _{DDIO} pins ⁽³⁾	200	
21	Total output current sourced (sum of all I/O and control pins) for devices with one V_{DDIO} pin ⁽³⁾	100	mA
Σl _{IO}	Total output current sunk (sum of all I/O and control pins) for devices with two $\rm V_{SSIO}$ pins $^{(3)}$	160	IIIA
	Total output current sunk (sum of all I/O and control pins) for devices with one V _{SSIO} pin ⁽³⁾	80	
	Injected current on NRST pin	±4	
I _{INJ(PIN)} (4)(5)	Injected current on OSCIN pin	±4	
	Injected current on any other pin ⁽⁶⁾	±4	
$\Sigma I_{\text{INJ(PIN)}}^{(4)}$	Total injected current (sum of all I/O and control pins) ⁽⁶⁾	±20	

- 1. Data based on characterization results, not tested in production.
- 2. All power (V_{DD} , V_{DDIO} , V_{DDA}) and ground (V_{SS} , V_{SSIO} , V_{SSA}) pins must always be connected to the external supply.
- I/O pins used simultaneously for high current source/sink must be uniformly spaced around the package between the V_{DDIO}/V_{SSIO} pins.
- $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. For true open-drain pads, there is no positive injection current, and the corresponding V_{IN} maximum must always be respected
- 5. Negative injection disturbs the analog performance of the device. See note in Section 10.3.10: 10-bit ADC characteristics on page 85.
- When several inputs are submitted to a current injection, the maximum $\Sigma I_{\text{INJ(PIN)}}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $\Sigma I_{\text{INJ(PIN)}}$ maximum current injection on four I/O port pins of the device.

Table 17. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-65 to 150	°C
T _J	Maximum junction temperature	150	C



10.3.3 External clock sources and timing characteristics

HSE user external clock

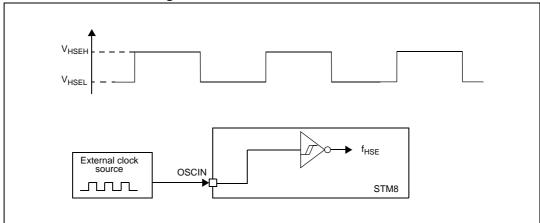
Subject to general operating conditions for V_{DD} and T_A .

Table 31. HSE user external clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSE_ext}	User external clock source frequency		0		24	MHz
V _{HSEH} ⁽¹⁾	OSCIN input pin high level voltage		0.7 x V _{DD}		V _{DD} + 0.3 V	V
V _{HSEL} ⁽¹⁾	OSCIN input pin low level voltage		V _{SS}		0.3 x V _{DD}	V
I _{LEAK_HSE}	OSCIN input leakage current	V _{SS} < V _{IN} < V _{DD}	-1		1	μΑ

^{1.} Data based on characterization results, not tested in production.

Figure 16. HSE external clock source



HSE crystal/ceramic resonator oscillator

The HSE clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

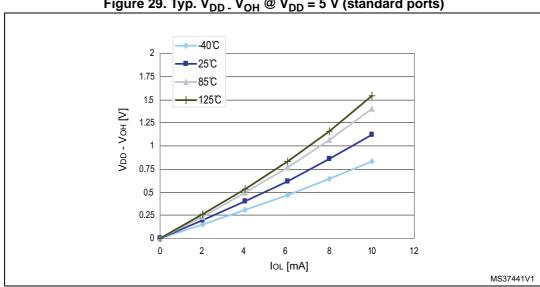
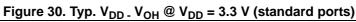
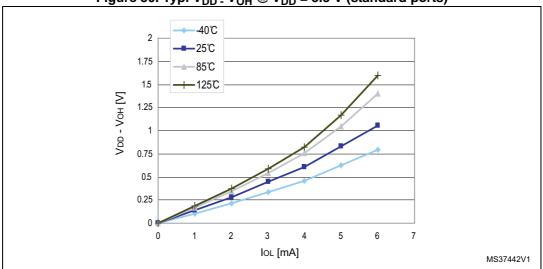


Figure 29. Typ. V_{DD} - V_{OH} @ V_{DD} = 5 V (standard ports)





76/117 DocID14733 Rev 13

10.3.7 Reset pin characteristics

Subject to general operating conditions for $V_{\mbox{\scriptsize DD}}$ and $T_{\mbox{\scriptsize A}}$ unless otherwise specified.

Table 41. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ ¹⁾	Max	Unit
V _{IL(NRST)}	NRST Input low level voltage (1)		-0.3 V		0.3 x V _{DD}	
V _{IH(NRST)}	NRST Input high level voltage (1)		0.7 x V _{DD}		V _{DD} + 0.3	V
V _{OL(NRST)}	NRST Output low level voltage (1)	I _{OL} = 2 mA			0.5	
R _{PU(NRST)}	NRST Pull-up resistor (2)		30	55	80	kΩ
t _{IFP(NRST)}	NRST Input filtered pulse (3)				75	ns
t _{INFP(NRST)}	NRST Input not filtered pulse (3)		500			ns
t _{OP(NRST)}	NRST output pulse (1)		15			μs

- 1. Data based on characterization results, not tested in production.
- 2. The R_{PU} pull-up equivalent resistor is based on a resistive transistor
- 3. Data guaranteed by design, not tested in production.

Figure 33. Typical NRST $\rm V_{IL}$ and $\rm V_{IH}$ vs $\rm V_{DD}$ @ 4 temperatures **-**40℃ 6 **—**25℃ ----85℃ 5 ----125℃ VIL - VIH [V] 2 0 2.5 6 3 3.5 4.5 5.5 VDD [V] MS37445V1

10.3.8 SPI serial peripheral interface

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under ambient temperature, f_{MASTER} frequency and V_{DD} supply voltage conditions. $t_{MASTER} = 1/f_{MASTER}$.

Refer to I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 42. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f _{SCK}	SDI alaak fraguanay	Master mode	0	10	MHz
1/t _{c(SCK)}	SPI clock frequency	Slave mode	0	6	IVITIZ
t _{r(SCK)}	SPI clock rise and fall time	Capacitive load: C = 30 pF		25	
t _{su(NSS)} ⁽¹⁾	NSS setup time	Slave mode	4 x t _{MASTER}		
t _{h(NSS)} ⁽¹⁾	NSS hold time	Slave mode	70		
t _{w(SCKH)} (1) t _{w(SCKL)} (1)	SCK high and low time	Master mode	t _{SCK} /2 - 15	t _{SCK} /2 + 15	
t _{su(MI)} (1) t _{su(SI)} (1)	Data input setup time	Master mode	5		
t _{su(SI)} ⁽¹⁾	Data input setup time	Slave mode	5		
t _{h(MI)} (1)	Data input hold time	Master mode	7		ns
t _{h(MI)} (1) t _{h(SI)} (1)	Data input hold time	Slave mode	10		
t _{a(SO)} (1)(2)	Data output access time	Slave mode		3 x t _{MASTER}	
t _{dis(SO)} (1)(3)	Data output disable time	Slave mode	25		
t _{v(SO)} (1)	Data output valid time	Slave mode (after enable edge)		75	
t _{v(MO)} ⁽¹⁾	Data output valid time	Master mode (after enable edge)		30	
t _{h(SO)} ⁽¹⁾	Data autaut hald time	Slave mode (after enable edge)	31		
t _{h(MO)} ⁽¹⁾	Data output hold time	Master mode (after enable edge)	12		

^{1.} Values based on design simulation and/or characterization results, and not tested in production.

^{2.} Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.

^{3.} Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

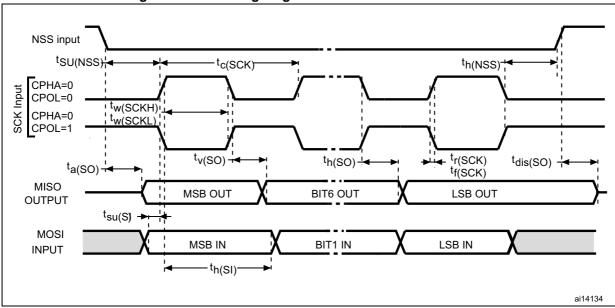
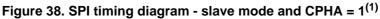
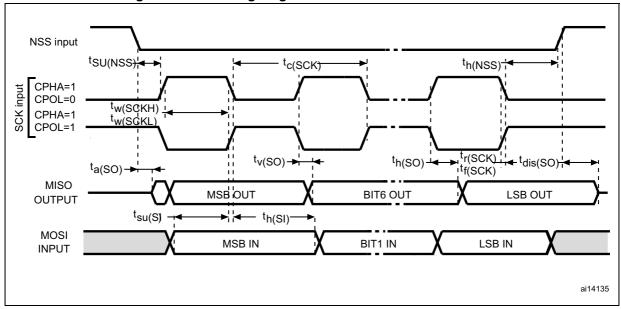


Figure 37. SPI timing diagram - slave mode and CPHA = 0





^{1.} Measurement points are done at CMOS levels: 0.3 $\rm V_{DD}$ and 0.7 $\rm V_{DD.}$

SAE EMI

level

Electromagnetic interference (EMI)

Emission tests conform to the SAE IEC 61967-2 standard for test software, board layout and pin loading.

Conditions Max f_{HSE}/f_{CPU}(1) **Symbol** Unit **Parameter** Monitored **General conditions** 8 MHz/ 8 MHz/ 8 MHz/ frequency band 8 MHz 16 MHz 24 MHz 0.1MHz to 30 MHz 20 24 $V_{DD} = 5 V$ Peak level $T_A = 25 \, ^{\circ}C$ 30 MHz to 130 MHz 18 21 16 dΒμV $\mathsf{S}_{\mathsf{EMI}}$ LQFP80 package 130 MHz to 1 GHz -1 1 4 conforming to SAE IEC

Table 48. EMI data

61967-2

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

SAE EMI level

2

2.5

2.5

Electrostatic discharge (ESD)

Electrostatic discharges (3 positive then 3 negative pulses separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 49. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (Human body model)	T _A = 25°C, conforming to JESD22-A114	Α	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (Charge device model)	T _A = 25°C, conforming to JESD22-C101	IV	1000	٧

^{1.} Data based on characterization results, not tested in production.



^{1.} Data based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on 10 parts to assess the latch-up performance:

- A supply overvoltage (applied to each power supply pin)
- A current injection (applied to each input, output and configurable I/O pin) is performed on each sample.

This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Table 50. Electrical sensitivities

Symbol	Parameter	Conditions	Class ⁽¹⁾
		T _A = 25 °C	Α
LU	Static latch-up class	T _A = 85 °C	А
		T _A = 125 °C	А

Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to class A it exceeds the JEDEC standard. B class strictly covers all the JEDEC criteria (international standard).

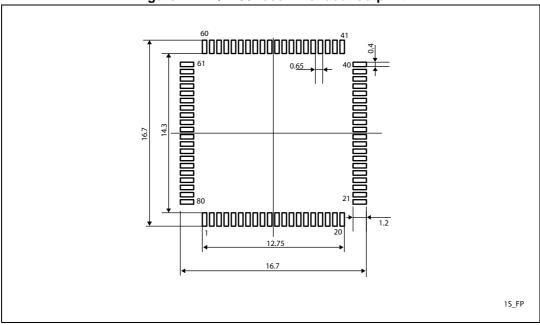
90/117 DocID14733 Rev 13

Table 51. LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package mechanical data⁽¹⁾ (continued)

Symbol	millimeters			inches		
	Min	Тур	Max	Min	Тур	Max
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.350	-	-	0.4862	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.350	-	-	0.4862	-
е	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.100	-	-	0.0039

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 44. LQFP80 recommended footprint



11.2 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 18: General operating conditions on page 56.*

The maximum chip-junction temperature, T_{Jmax} , in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum ambient temperature in °C
- Θ_{JA} is the package junction-to-ambient thermal resistance in ° C/W
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum power dissipation on output pins, where: $P_{I/Omax} = \sum (V_{OL}^*I_{OL}) + \sum ((V_{DD}^-V_{OH})^*I_{OH})$, and taking account of the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit			
Θ_{JA}	Thermal resistance junction-ambient LQFP 80 - 14 x 14 mm	38	°C/W			
Θ_{JA}	Thermal resistance junction-ambient LQFP 64 - 14 x 14 mm	45	°C/W			
Θ_{JA}	Thermal resistance junction-ambient LQFP 64 - 10 x 10 mm	46	°C/W			
Θ_{JA}	Thermal resistance junction-ambient LQFP 48 - 7 x 7 mm	57	°C/W			
Θ_{JA}	Thermal resistance junction-ambient LQFP 44 - 10 x 10 mm	54	°C/W			
Θ_{JA}	Thermal resistance junction-ambient LQFP 32 - 7 x 7 mm	60	°C/W			

Table 57. Thermal characteristics⁽¹⁾

11.2.1 Reference document

JESD51-2 integrated circuits thermal test method environment conditions - natural convection (still air). Available from www.jedec.org.

577

108/117 DocID14733 Rev 13

Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

14 Revision history

Table 58. Document revision history

Date	Revision	Changes	
23-May-2008	1	Initial release.	
05-Jun-2008	2	Added part numbers on page 1 and in <i>Table 2 on page 11</i> . Updated <i>Section 4: Product overview</i> . Updated <i>Section 10: Electrical characteristics</i> .	
22-Jun-2008	3	Added part numbers on page 1 and in Table 2 on page 11.	
12-Aug-2008	4	Added 32 pin device pinout and ordering information. Updated UBC option description in <i>Table 13 on page 48</i> . USART renamed UART1, LINUART renamed UART3. Max. ADC frequency increased to 6 MHz.	
20-Oct-2008	5	Removed STM8S207K4 part number. Removed LQFP64 14 x 14 mm package. Added medium and high density Flash memory categories. Added Section 6: Memory and register map on page 34. Replaced beCAN3 by beCAN in Section 4.14.5: beCAN. Updated Section 10: Electrical characteristics on page 52. Updated LQFP44 (Figure 53 and Table 55), and LQFP32 outline and mechanical data (Figure 56, and Table 56).	
08-Dec-2008	6	Changed V _{DD} minimum value from 3.0 to 2.95 V. Updated number of High Sink I/Os in pinout. Removed FLASH _NFPR and FLASH _FPR registers in <i>Table 9: General hardware register map</i> .	
30-Jan-2009	7	Removed preliminary status. Removed VQFN32 package. Added STM8S207C6, STM8S207S6. Updated external interrupts in <i>Table 2 on page 11</i> . Updated <i>Section 10: Electrical characteristics</i> .	
10-Jul-2009	8	Document status changed from "preliminary data" to "datasheet". Added LQFP64 14 x 14 mm package. Added STM8S207M8, STM8S207SB, STM8S208R8, STM8S208R6, STM8S208C8, and STM8S208C6, STM8S208SB, STM8S208S8, and STM8S208S6. Replaced "CAN" with "beCAN". Added Table 3 to Section 4.5: Clock controller. Updated Section 4.8: Auto wakeup counter. Added beCAN peripheral (impacting Table 1 and Figure 6). Added footnote about CAN_RX/TX to pinout figures 5, 4, and 6. Table 6: Removed 'X' from wpu column of I ² C pins (no wpu available). Added Table 11: Interrupt mapping.	

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